

2. (Amended) A method for producing a silicon semiconductor wafer comprising

pulling a silicon single crystal from a melt, in the presence of hydrogen, using the Czochralski method, wherein the silicon single crystal is pulled under a hydrogen partial pressure of less than 3 mbar;

doping the silicon single crystal with nitrogen and producing a nitrogen concentration of 5×10^{12} atcm⁻³ to 5×10^{15} atcm⁻³; and

separating the silicon semiconductor wafer from the silicon single crystal.

REMARKS

Reconsideration of this patent application is respectfully requested in view of the foregoing amendments, and the following remarks.

The Patent Examiner has rejected all the claims 1 to 6 as being anticipated or unpatentable over the following prior art references in various combinations thereof: namely Jacob DE